BT139F series E

### **GENERAL DESCRIPTION**

# Glass passivated, sensitive gate triacs in a full pack plastic envelope, intended for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants.

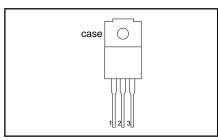
### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
$V_{DRM}$	BT139F- Repetitive peak off-state	<b>500E</b> 500	<b>600E</b> 600	<b>800E</b> 800	V
I <sub>T(RMS)</sub> I <sub>TSM</sub>	voltages RMS on-state current Non-repetitive peak on-state current	16 140	16 140	16 140	A A

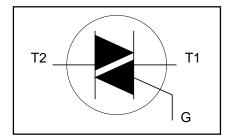
### **PINNING - SOT186**

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
case	isolated

### **PIN CONFIGURATION**



### **SYMBOL**



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
$V_{DRM}$	Repetitive peak off-state voltages		-	<b>-500</b> 500 <sup>1</sup>	<b>-600</b> 600 <sup>1</sup>	<b>-800</b> 800	V
I <sub>T(RMS)</sub> I <sub>TSM</sub>	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{hs} \le 38 ^{\circ}\text{C}$ full sine wave; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{DRM(max)}$	-		16		А
		t = 20 ms	-		140		A
124	124 for funcion	t = 16.7 ms	-		150		A A22
l²t dl <sub>⊤</sub> /dt	I <sup>2</sup> t for fusing Repetitive rate of rise of on-state current after	t = 10  ms $  I_{TM} = 20 \text{ A};   I_G = 0.2 \text{ A}; $ $  d I_G / dt = 0.2 \text{ A} / \mu \text{s} $	-		98		A <sup>2</sup> s
	triggering	T2+ G+	-		50		A/μs
		T2+ G-	-		50		A/μs
		T2- G-	-		50		A/μs
١,	Dook goto gurrant	T2- G+	-		10		A/μs
I <sub>GM</sub>	Peak gate current Peak gate voltage		_		5		A
V <sub>GM</sub> P <sub>GM</sub>	Peak gate power		_		5		ĺ ẇ́
P <sub>G(AV)</sub> T <sub>stg</sub> T <sub>j</sub>	Average gate power Storage temperature Operating junction temperature	over any 20 ms period	-40 -		0.5 150 125		Ç Ç W

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<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15  $A/\mu s$ .

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### **ISOLATION LIMITING VALUE & CHARACTERISTIC**

 $T_{hs}$  = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>isol</sub>	Repetitive peak voltage from all three terminals to external heatsink	R.H. ≤ 65% ; clean and dustfree	ı		1500	>
C <sub>isol</sub>	Capacitance from T2 to external heatsink	f = 1 MHz	-	12	1	pF

### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-hs</sub>	Thermal resistance junction to heatsink Thermal resistance	full or half cycle with heatsink compound without heatsink compound in free air	-	- - 55	4.0 5.5	K/W K/W K/W
I ¹ <b>`</b> th i-a	junction to ambient	iii iice aii	•	J5	•	17/17

### STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

) = 20 °C unicoo outorwise stated						
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>GT</sub>	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$				
		T2+ G+	-	2.5	10	mΑ
		T2+ G-	-	4.0	10	mΑ
		T2- G-	-	5.0	10	mΑ
		T2- G+	-	11	25	mΑ
I <sub>L</sub>	Latching current	$V_{\rm D} = 12 \text{ V}; I_{\rm GT} = 0.1 \text{ A}$				
-	_	T2+ G+	-	3.2	30	mΑ
		T2+ G-	-	16	40	mA
		T2- G-	-	4.0	30	mA
		T2- G+	-	5.5	40	mA
l I <sub>H</sub>	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	4.0	30	mΑ
V <sub>T</sub>	On-state voltage	$I_{T} = 20 \text{ A}$	-	1.2	1.6	V
V <sub>GT</sub>	Gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$		0.7	1.5	V
1.		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_L = 125 \text{ °C}$	0.25	0.4		V <sub>.</sub>
l I <sub>D</sub>	Off-state leakage current	$V_D = V_{DRM(max)}$ ; $T_j = 125  ^{\circ}C$	-	0.1	0.5	mA

### **DYNAMIC CHARACTERISTICS**

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
	Critical rate of rise of off-state voltage	V <sub>DM</sub> = 67% V <sub>DRM(max)</sub> ; T <sub>j</sub> = 125 °C; exponential waveform; gate open circuit	-	50	1	V/μs
t <sub>gt</sub>	Gate controlled turn-on time	$V_D = V_{DRM(max)}$ ; $I_G = 0.1$ A; $dI_G/dt = 5$ A/ $\mu$ s; $I_{TM} = 20$ A	-	2	-	μs

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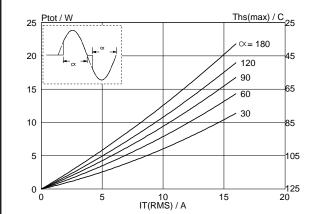


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha = conduction$  angle.

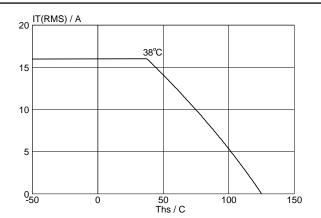


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus heatsink temperature  $T_{hs}$ .

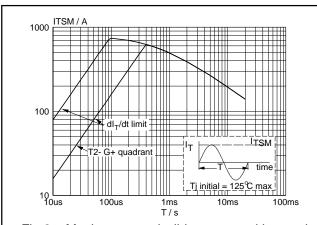


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 20$ ms.

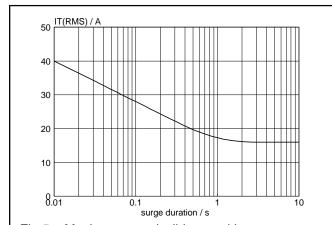


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{hs} \le 38$  °C.

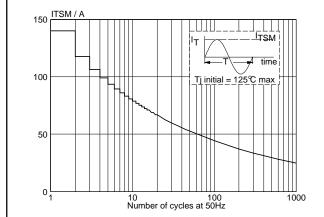


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

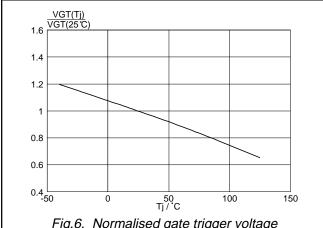
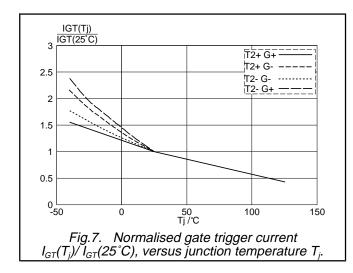
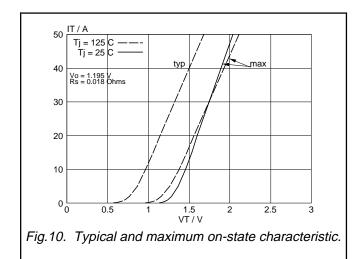
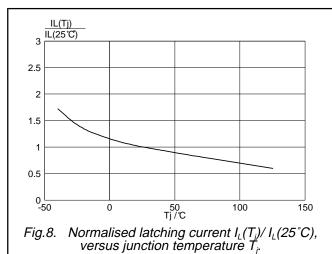


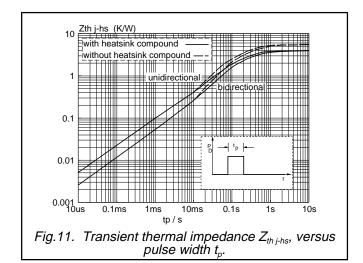
Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j)/V_{GT}(25\,^{\circ}C)$ , versus junction temperature  $T_j$ .

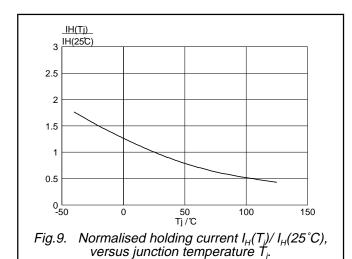
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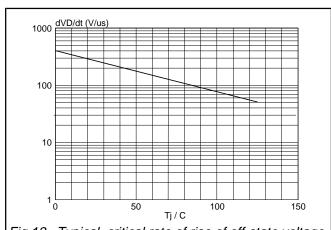
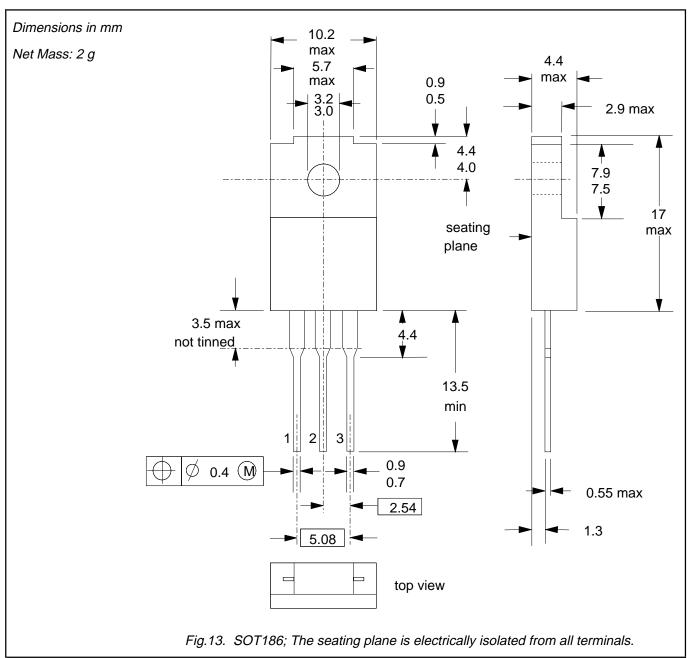


Fig.12. Typical, critical rate of rise of off-state voltage, dV<sub>D</sub>/dt versus junction temperature T<sub>i</sub>.

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### **MECHANICAL DATA**



- Accessories supplied on request: refer to mounting instructions for F-pack envelopes.
   Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

### Triacs sensitive gate

BT139F series E

### **DEFINITIONS**

Data sheet status					
Objective specification	This data sheet contains target or goal specifications for product development.				
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				

#### Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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